

Effect on the Mg₂Si Synthesized by Solid State Reaction and Hot Pressing Process

Thursday, May 21, 2015 1:00 PM (3h 30m)

Metal/semiconductor Mg₂Si compounds was synthesized by solid state reaction method. The sample was calcined at temperature 973 K in vacuum system. It was pressed into pellet, and then was sintered in hot-pressing process at 973 K. The Mg₂Si was studied structure properties by XRD and SEM, electrical properties by Hall Effect at room temperature and thermal properties by laser flash method at 300 up to 500 K. Finally, the results of normal process and hot-pressing process effect on thermal conductivity were compared and reported.

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Session Classification: Poster-3

Track Classification: Material Physics, Nanoscale Physics and Nanotechnology